

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. - 21. (Cancelled)

22. (Currently Amended) A capacitor of a semiconductor device, the capacitor comprising:

a lower electrode;

an AHO((Al<sub>x</sub>Hf<sub>1-x</sub>)O<sub>y</sub>) film formed on the lower electrode;

an upper electrode formed on the AHO film; and

a dielectric film having a dielectric constant that is higher than that of the AHO film between the upper electrode and the AHO layer,

wherein the dielectric film is an HfO<sub>2</sub> layer, a ZrO<sub>2</sub> layer, or an STO layer.

23. (Original) The capacitor of claim 22, further comprising an oxidation barrier film formed between the lower electrode and the AHO layer.

24. - 37. (Cancelled)